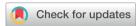
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## CORRECTION

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## Correction: Interfacial engineering of a Mo/Hf<sub>0.3</sub>Zr<sub>0.7</sub>O<sub>2</sub>/Si capacitor using the direct scavenging effect of a thin Ti layer

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Correction for 'Interfacial engineering of a Mo/Hf<sub>0.3</sub>Zr<sub>0.7</sub>O<sub>2</sub>/Si capacitor using the direct scavenging effect of a thin Ti layer' by Se Hyun Kim et al., Chem. Commun., 2021, 57, 12452-12455, https://doi. org/10.1039/D1CC04966F.

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